



Welcome to **E-XFL.COM** 

**Understanding Embedded - CPLDs (Complex Programmable Logic Devices)** 

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

#### **Applications of Embedded - CPLDs**

Details	
Product Status	Obsolete
Programmable Type	EE PLD
Delay Time tpd(1) Max	10 ns
Voltage Supply - Internal	3V ~ 3.6V
Number of Logic Elements/Blocks	-
Number of Macrocells	8
Number of Gates	-
Number of I/O	-
Operating Temperature	0°C ~ 75°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LCC (J-Lead)
Supplier Device Package	20-PLCC (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/gal16lv8c-10ljn

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong





# GAL16LV8

Low Voltage E<sup>2</sup>CMOS PLD Generic Array Logic™

### **Features**

- HIGH PERFORMANCE E2CMOS® TECHNOLOGY
- 3.5 ns Maximum Propagation Delay
- -Fmax = 250 MHz
- 2.5 ns Maximum from Clock Input to Data Output
- UltraMOS® Advanced CMOS Technology
- 3.3V LOW VOLTAGE 16V8 ARCHITECTURE
- JEDEC-Compatible 3.3V Interface Standard
- 5V Compatible Inputs
- I/O Interfaces with Standard 5V TTL Devices (GAL16LV8C)
- ACTIVE PULL-UPS ON ALL PINS (GAL16LV8D Only)
- E<sup>2</sup> CELL TECHNOLOGY
  - Reconfigurable Logic
  - Reprogrammable Cells
  - 100% Tested/100% Yields
  - High Speed Electrical Erasure (<100ms)
  - 20 Year Data Retention
- EIGHT OUTPUT LOGIC MACROCELLS
  - Maximum Flexibility for Complex Logic Designs
  - Programmable Output Polarity
- PRELOAD AND POWER-ON RESET OF ALL REGISTERS
  - 100% Functional Testability
- APPLICATIONS INCLUDE:
  - Glue Logic for 3.3V Systems
  - DMA Control
  - State Machine Control
  - High Speed Graphics Processing
  - Standard Logic Speed Upgrade
- ELECTRONIC SIGNATURE FOR IDENTIFICATION
- LEAD-FREE PACKAGE OPTIONS

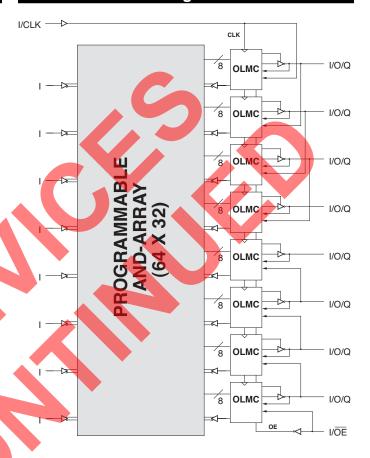
### Description

The GAL16LV8D, at 3.5 ns maximum propagation delay time, provides the highest speed performance available in the PLD market. The GAL16LV8C can interface with both 3.3V and 5V signal levels. The GAL16LV8 is manufactured using Lattice Semiconductor's advanced 3.3V E<sup>2</sup>CMOS process, which combines CMOS with Electrically Erasable (E<sup>2</sup>) floating gate technology. High speed erase times (<100ms) allow the devices to be reprogrammed quickly and efficiently.

The 3.3V GAL16LV8 uses the same industry standard 16V8 architecture as its 5V counterpart and supports all architectural features such as combinatorial or registered macrocell operations.

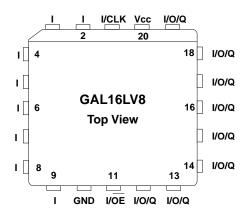
Unique test circuitry and reprogrammable cells allow complete AC, DC, and functional testing during manufacture. As a result, Lattice Semiconductor delivers 100% field programmability and functionality of all GAL products. In addition, 100 erase/write cycles and data retention in excess of 20 years are specified.

## Functional Block Diagram



## **Pin Configuration**

### **PLCC**



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August 2004

16lv8\_05



## **GAL16LV8 Ordering Information**

# Conventional Packaging Commercial Grade Specifications

Tpd (ns)	Tsu (ns)	Tco (ns)	Icc (mA)	Ordering #	Package
3.5	3	2.5	70	GAL16LV8D-3LJ	20-Lead PLCC
5	4	3	70	GAL16LV8D-5LJ	20-Lead PLCC
7.5	6	5	65	GAL16LV8C-7LJ <sup>1</sup>	20-Lead PLCC
10	7	7	65	GAL16LV8C-10LJ	20-Lead PLCC
15	12	10	65	GAL16LV8C-15LJ	20-Lead PLCC

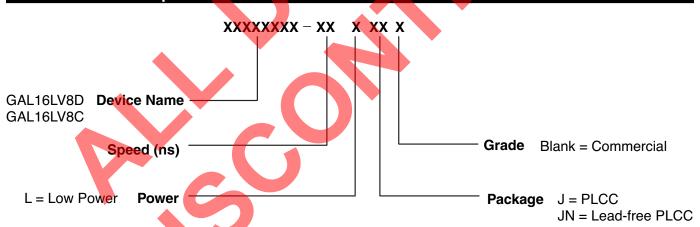
## **Lead-Free Packaging**

## **Commercial Grade Specifications**

Tpd (ns)	Tsu (ns)	Tco (ns)	Icc (mA)	Ordering #	Package
3.5	3	2.5	70	GAL16LV8D-3LJN	Lead-Free 20-Lead PLCC
5	4	3	70	GAL16LV8D-5LJN	Lead-Free 20-Lead PLCC
7.5	6	5	65	GAL16LV8C-7LJN <sup>1</sup>	Lead-Free 20-Lead PLCC
10	7	7	65	GAL16LV8C-10LJN	Lead-Free 20-Lead PLCC
15	12	10	65	GAL16LV8C-15LJN	Lead-Free 20-Lead PLCC

<sup>1.</sup> Discontinued per PCN #06-07. Contact Rochester Electronics for available inventory.

# **Part Number Description**



## **Registered Mode**

In the Registered mode, macrocells are configured as dedicated registered outputs or as I/O functions.

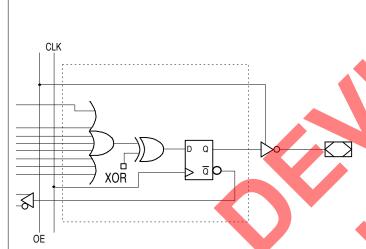
Architecture configurations available in this mode are similar to the common 16R8 and 16RP4 devices with various permutations of polarity, I/O and register placement.

All registered macrocells share common clock and output enable control pins. Any macrocell can be configured as registered or I/O. Up to eight registers or up to eight I/Os are possible in this mode.

Dedicated input or output functions can be implemented as subsets of the I/O function.

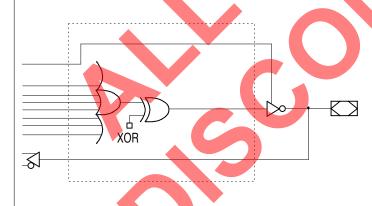
Registered outputs have eight product terms per output. I/Os have seven product terms per output.

The JEDEC fuse numbers, including the User Electronic Signature (UES) fuses and the Product Term Disable (PTD) fuses, are shown on the logic diagram on the following page.



### Registered Configuration for Registered Mode

- SYN=0.
- AC0=1.
- XOR=0 defines Active Low Output.
- XOR=1 defines Active High Output.
- AC1=0 defines this output configuration.
- Pin 1 controls common CLK for the registered outputs.
- Pin 11 controls common  $\overline{OE}$  for the registered outputs.
- Pin 1 & Pin 11 are permanently configured as CLK &
- OE for registered output configuration.



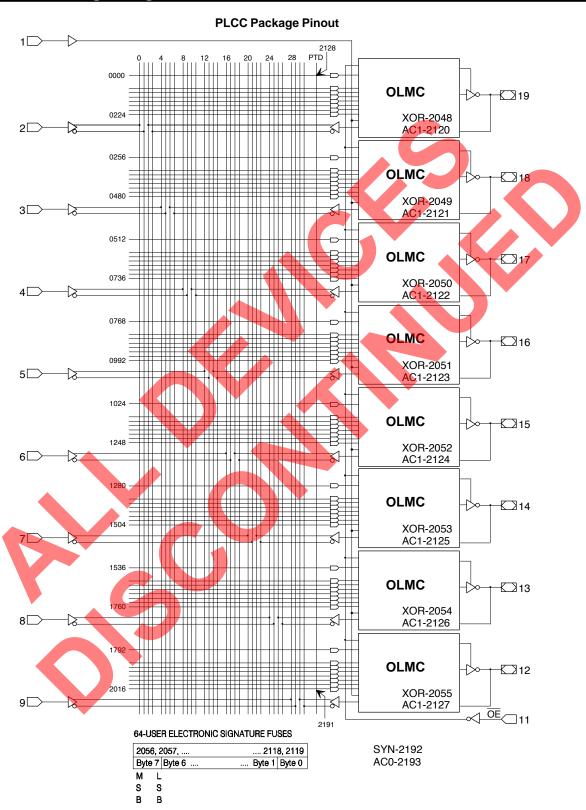
#### Combinatorial Configuration for Registered Mode

- SYN=0.
- AC0=1.
- XOR=0 defines Active Low Output.
- XOR=1 defines Active High Output.
- AC1=1 defines this output configuration.
- Pin 1 & Pin 11 are permanently configured as CLK & OE for registered output configuration.

Note: The development software configures all of the architecture control bits and checks for proper pin usage automatically.



## Registered Mode Logic Diagram





## **Complex Mode**

In the Complex mode, macrocells are configured as output only or I/O functions.

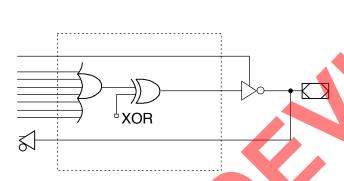
Architecture configurations available in this mode are similar to the common 16L8 and 16P8 devices with programmable polarity in each macrocell.

Up to six I/Os are possible in this mode. Dedicated inputs or outputs can be implemented as subsets of the I/O function. The two outer most macrocells (pins 12 & 19) do not have input capability. De-

signs requiring eight I/Os can be implemented in the Registered mode

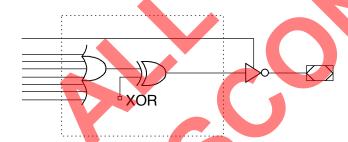
All macrocells have seven product terms per output. One product term is used for programmable output enable control. Pins 1 and 11 are always available as data inputs into the AND array.

The JEDEC fuse numbers including the UES fuses and PTD fuses are shown on the logic diagram on the following page.



#### Combinatorial I/O Configuration for Complex Mode

- SYN=1
- AC0=1.
- XOR=0 defines Active Low Output.
- XOR=1 defines Active High Output.
- AC1=1.
- Pin 13 through Pin 18 are configured to this function.



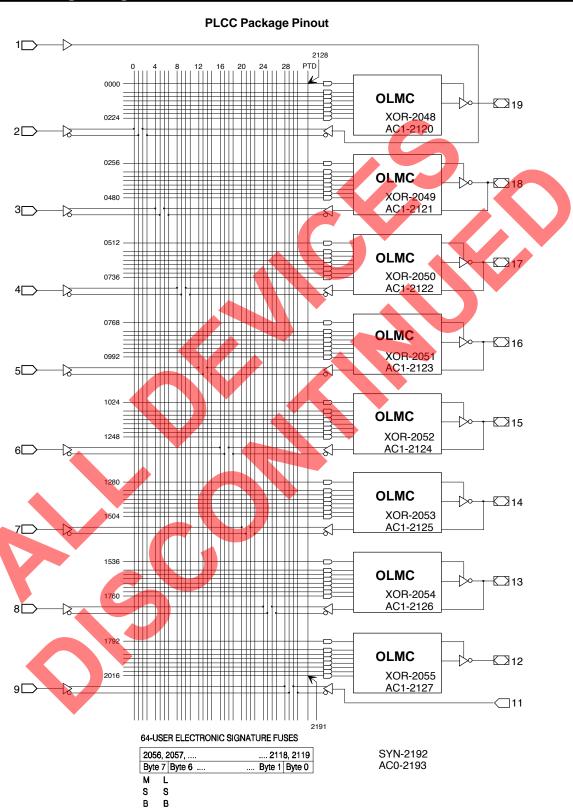
#### Combinatorial Output Configuration for Complex Mode

- SYN=1.
- AC0=1.
- XOR=0 defines Active Low Output.
- XOR=1 defines Active High Output.
- AC1=1.
- Pin 12 and Pin 19 are configured to this function.

Note: The development software configures all of the architecture control bits and checks for proper pin usage automatically.

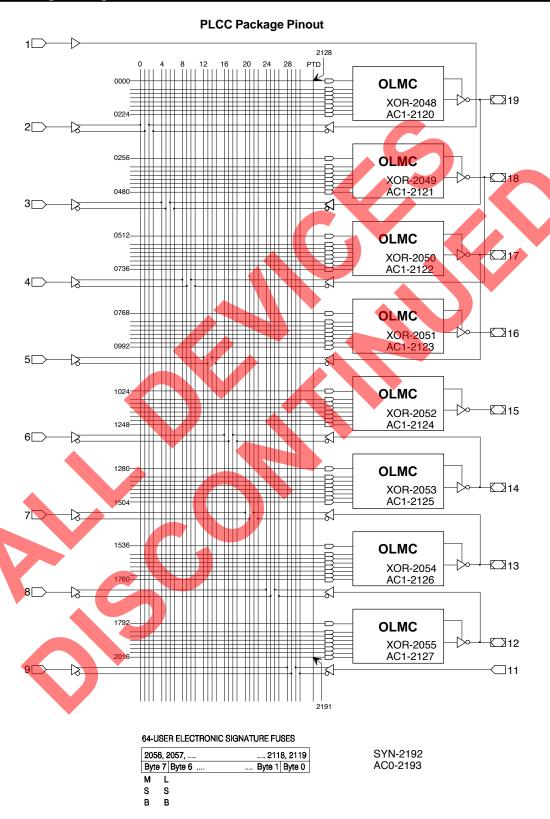


## Complex Mode Logic Diagram





## Simple Mode Logic Diagram





## **Absolute Maximum Ratings**(1)

Supply voltage V <sub>cc</sub>	0.5 to +4.6V
Input voltage applied	0.5 to +5.6V
I/O voltage applied	0.5 to +4.6V
Off-state output voltage applied	0.5 to +4.6V
Storage Temperature	–65 to 150°C
Ambient Temperature with	
Power Applied	–55 to 125°C

1.Stresses above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress only ratings and functional operation of the device at these or at any other conditions above those indicated in the operational sections of this specification is not implied (while programming, follow the programming specifications).

# **Recommended Operating Conditions**

#### **Commercial Devices:**

Ambient Temperature (T <sub>A</sub> )	0 to 75°C
Supply voltage (V <sub>CC</sub> )	
with Respect to Ground	+3.0 to +3.6V



### **DC Electrical Characteristics**

### Over Recommended Operating Conditions (Unless Otherwise Specified)

SYMBOL	PARAMETER	CONDITION	MIN.	TYP.3	MAX.	UNITS
<b>V</b> IL	Input Low Voltage		Vss - 0.3	_	0.8	V
<b>V</b> IH	Input High Voltage		2.0	_	5.25	V
	I/O High Voltage		2.0	ı	Vcc+0.5	V
IIL¹	Input or I/O Low Leakage Current	0V ≤ VIN ≤ VIL (MAX.)	_	I	-100	μΑ
Iн	Input or I/O High Leakage Current	(Vcc-0.2)V ≤ VIN ≤ Vcc	_	1	10	μΑ
	Input High Leakage Current	Vcc ≤ VIN ≤ 5.25V	_	1	10	μΑ
	I/O High Leakage Current	VCC ≤ VIN≤ 4.6V	_	-	20	mA
<b>V</b> OL	Output Low Voltage	IOL = MAX. Vin = VIL or VIH	_	ı	0.4	V
		<b>J</b> oL = 500μ <b>A Vin</b> = <b>V</b> IL or <b>V</b> IH		-	0.2	V
<b>V</b> OH	Output High Voltage	IOH = MAX. Vin = VIL or VIH	2.4	_	_	V
		Іон = -100μA Vin = V <sub>IL</sub> or V <sub>I</sub> H	<b>V</b> cc-0.2V	_	_	V
<b>I</b> OL	Low Level Output Current		_	_	8	mA
<b>І</b> он	High Level Output Current		_	_	-8	mA
los <sup>2</sup>	Output Short Circuit Current	<b>V</b> cc = 3.3V <b>V</b> out = 0.5V T <sub>A</sub> = 25°C	-15	_	-80	mA

### COMMERCIAL

Icc	Operating Power	V <sub>IL</sub> = 0V V <sub>IH</sub> = 3.0V Unused Inputs at V <sub>IL</sub>	_	45	70	mA
	Supply Current	ftoggle = 1MHz Outputs Open				

<sup>1)</sup> The leakage current is due to the internal pull-up resistor on all pins. See Input Buffer section for more information.

<sup>2)</sup> One output at a time for a maximum duration of one second. Vout = 0.5V was selected to avoid test problems caused by tester ground degradation. Characterized but not 100% tested.

<sup>3)</sup> Typical values are at Vcc = 3.3V and T<sub>A</sub> = 25 °C

## **AC Switching Characteristics**

## **Over Recommended Operating Conditions**

			C	MC	CC	MC	
DADAMETED	TEST	DESCRIPTION	-:	3	-5		UNITS
PARAMETER	COND <sup>1</sup> .	DESCRIPTION	MIN.	MAX.	MIN.	MAX.	UNITS
<b>t</b> pd <sup>2</sup>	Α	Input or I/O to Combinational Output	1	3.5	1	5	ns
tco <sup>2</sup>	Α	Clock to Output Delay	1	2.5	1	3	ns
<b>t</b> cf³	_	Clock to Feedback Delay		2	_	2	ns
<b>t</b> su	_	Setup Time, Input or Feedback before Clock↑	3	_	4	-	ns
<b>t</b> h	_	Hold Time, Input or Feedback after Clock↑	0		0	_	ns
	А	Maximum Clock Frequency with External Feedback, 1/(tsu + tco)	180		142.8	-	MHz
<b>f</b> max⁴	А	Maximum Clock Frequency with Internal Feedback, 1/(tsu + tcf)	200	-	166	_	MHz
	А	Maximum Clock Frequency with No Feedback	250	-	166	_	MHz
<b>t</b> wh⁴	_	Clock Pulse Duration, High	2	_	3	_	ns
<b>t</b> wl⁴	_	Clock Pulse Duration, Low	2	_	3	_	ns
<b>t</b> en	В	Input or I/O to Output Enabled	_	4.5	_	6	ns
	В	OE to Output Enabled	_	3.5	_	5	ns
<b>t</b> dis	С	Input or I/O to Output Disabled	_	4.5	_	6	ns
	С	OE to Output Disabled	_	3.5	_	5	ns

- 1) Refer to Switching Test Conditions section.
- 2) Minimum values for tpd and tco are not 100% tested but established by characterization.
- 3) Calculated from fmax with internal feedback. Refer to fmax Descriptions section.
- 4) Refer to fmax Descriptions section. Characterized but not 100% tested.

# Capacitance $(T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$

SYMBOL	PARAMETER	TYPICAL	UNITS	TEST CONDITIONS
C <sub>i</sub>	Input Capacitance	5	pF	$V_{CC} = 3.3V, V_{I} = 0V$
C <sub>I/O</sub>	I/O Capacitance	5	pF	$V_{CC} = 3.3V, V_{I/O} = 0V$



# Absolute Maximum Ratings(1)

Supply voltage V <sub>CC</sub>	0.5 to +5.6V
Input voltage applied	0.5 to +5.6V
Off-state output voltage applied	0.5 to +5.6V
Storage Temperature	65 to 150°C
Ambient Temperature with	
Power Applied	55 to 125°C

1. Stresses above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress only ratings and functional operation of the device at these or at any other conditions above those indicated in the operational sections of this specification is not implied (while programming, follow the programming specifications).

## **Recommended Operating Conditions**

#### **Commercial Devices:**

Ambient Temperature (T <sub>A</sub> )	0 to 75°C
Supply voltage (V <sub>CC</sub> )	
with Respect to Ground +	-3.0 to +3.6V

# **DC Electrical Characteristics**

### Over Recommended Operating Conditions (Unless Otherwise Specified)

SYMBOL	PARAMETER	CONDITION	MIN.	TYP. <sup>2</sup>	MAX.	UNITS
<b>V</b> IL	Input Low Voltage		Vss - 0.5	_	0.8	V
<b>V</b> IH	Input High Voltage		2.0	_	5.25	V
<b>I</b> IL	Input or I/O Low Leakage Current	0V ≤ VIN ≤ VIL (MAX.)	_	_	-10	μА
Iн	Input or I/O High Leakage Current	(Vcc - 0.2)V ≤ ViN ≤ Vcc	_	_	10	μΑ
		Vcc ≤ Vin ≤ 5.25V	_	_	30	mA
<b>V</b> OL	Output Low Voltage	IOL = MAX. Vin = VIL or VIH	_	_	0.4	V
		<b>Ι</b> ο∟ = 500 μΑ <b>V</b> in = <b>V</b> ι∟ or <b>V</b> ι⊢	_	_	0.2	V
<b>V</b> OH	Output High Voltage	Ioh = MAX. Vin = VIL or VIH	2.4	_	_	V
		<b>I</b> OH = -500 μA <b>V</b> in = <b>V</b> IL or <b>V</b> IH	Vcc-0.45	_	_	V
		<b>l</b> oн = -100 μA <b>V</b> in = <b>V</b> <sub>IL</sub> or <b>V</b> <sub>IH</sub>	Vcc-0.2	_	_	V
<b>I</b> OL	Low Level Output Current		_	_	8	mA
<b>І</b> он	High Level Output Current		_	_	-4	mA
los¹	Output Short Circuit Current	<b>V</b> cc = 3.3V <b>V</b> out = 0.5V <b>T</b> A = 25°C	-10	_	-60	mA

# COMMERCIAL

<b>I</b> cc	Operating Power	<b>V</b> <sub>IL</sub> = 0.0V <b>V</b> <sub>IH</sub> = 3.0V	_	45	65	mA
	Supply Current	f <sub>toggle</sub> = 1MHz Outputs Open				

<sup>1)</sup> One output at a time for a maximum duration of one second. Vout = 0.5V was selected to avoid test problems by tester ground degradation. Characterized but not 100% tested.

<sup>2)</sup> Typical values are at Vcc = 3.3V and  $T_A = 25$  °C



# **AC Switching Characteristics**

## Over Recommended Operating Conditions (Unless Otherwise Specified)

			CC	M	CC	OM	CC	MC	
DADAMETED	TEST	DESCRIPTION	-7		-10		-15		
PARAMETER	COND <sup>1</sup> .		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	UNITS
<b>t</b> pd <sup>2</sup>	Α	Input or I/O to Combinational Output	1	7.5	1	10	1	15	ns
tco <sup>2</sup>	Α	Clock to Output Delay	1	5	1	7	1	10	ns
<b>t</b> cf³	_	Clock to Feedback Delay	<b>_</b>	4	7	5	_	8	ns
<b>t</b> su	_	Setup Time, Input or Feedback before Clock↑	6	4	7	_	12	-	ns
<b>t</b> h	_	Hold Time, Input or Feedback after Clock↑	0		0		0		ns
	A	Maximum Clock Frequency with External Feedback, 1/(tsu + tco)	90.9	_	71.4		45.5		MHz
<b>f</b> max⁴	Α	Maximum Clock Frequency with Internal Feedback, 1/(tsu + tcf)	100	-	83.3	-	50	_	MHz
	A	Maximum Clock Frequency with No Feedback	100		83.3	-	62.5	_	MHz
<b>t</b> wh	_	Clock Pulse Duration, High	5		6	_	8	_	ns
<b>t</b> wl	_	Clock Pulse Duration, Low	5	_	6	_	8	_	ns
<b>t</b> en	В	Input or I/O to Output Enabled	<b>\rightarrow</b>	9	_	10	_	15	ns
	В	OE to Output Enabled	_	6	_	8	_	15	ns
<b>t</b> dis	С	Input or I/O to Output Disabled	_	9	_	10	_	15	ns
	С	OE to Output Disabled	_	6	_	8	_	15	ns

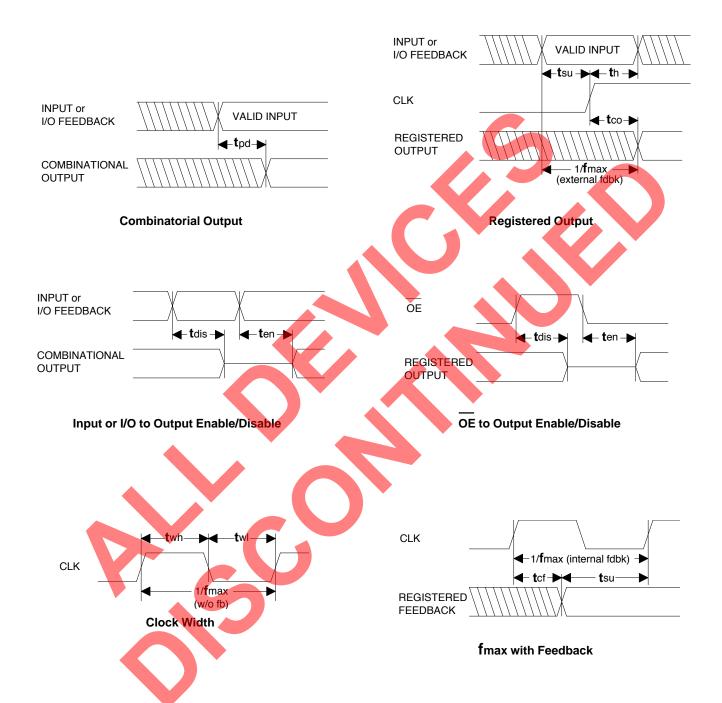
- 1) Refer to **Switching Test Conditions** section.
- 2) Minimum values for tpd and tco are not 100% tested but established by characterization.
- 3) Calculated from fmax with internal feedback. Refer to fmax Descriptions section.
- 4) Refer to fmax Descriptions section. Characterized but not 100% tested.

# Capacitance $(T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$

SYMBOL	PARAMETER	TYPICAL	UNITS	TEST CONDITIONS
Cı	Input Capacitance	8	pF	$V_{CC} = 3.3V, V_{I} = 0V$
C <sub>I/O</sub>	I/O Capacitance	8	pF	$V_{CC} = 3.3V, V_{I/O} = 0V$

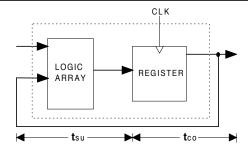


## **Switching Waveforms**



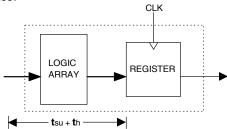


# fmax Descriptions



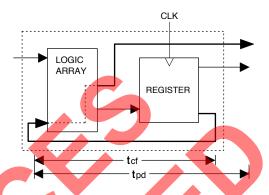
### fmax with External Feedback 1/(tsu+tco)

**Note:** fmax with external feedback is calculated from measured tsu and tco.



fmax with No Feedback

Note: fmax with no feedback may be less than 1/(twh+twl). This is to allow for a clock duty cycle of other than 50%.



## fmax with Internal Feedback 1/(tsu+tcf)

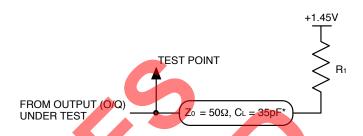
**Note:** tcf is a calculated value, derived by subtracting tsu from the period of fmax w/internal feedback (tcf = 1/fmax - tsu). The value of tcf is used primarily when calculating the delay from clocking a register to a combinatorial output (through registered feedback), as shown above. For example, the timing from clock to a combinatorial output is equal to tcf + tpd.

# **GAL16LV8D: Switching Test Conditions**

Input Pulse Levels	GND to 3.0V		
Input Rise and Fall Times	1.5ns 10% – 90%		
Input Timing Reference Levels	1.5V		
Output Timing Reference Levels	1.5V		
Output Load	See Figure		

#### **GAL16LV8D Output Load Conditions (see figure)**

Tes	t Condition	R <sub>1</sub>	CL
Α		50Ω	35pF
В	High Z to Active High at 1.9V	50Ω	35pF
	High Z to Active Low at 1.0V	50Ω	35pF
С	Active High to High Z at 1.9V	50Ω	35pF
	Active Low to High Z at 1.0V	50Ω	35pF



\*C, INCLUDES TEST FIXTURE AND PROBE CAPACITANCE

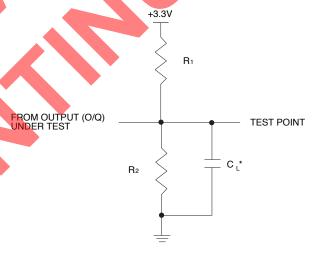
# **GAL16LV8C: Switching Test Conditions**

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	1.5ns 10% – 90%
Input Timing Reference Levels	1.5V
Output Timing Reference Levels	1.5V
Output Load	See Figure

3-state levels are measured 0.5V from steady-state active level.

## GAL16LV8C Output Load Conditions (see figure)

Tes	t Condition	R <sub>1</sub>	R <sub>2</sub>	CL
Α		316Ω	348Ω	35pF
В	Active High	$316\Omega$	348Ω	35pF
	Active Low	316Ω	348Ω	3 <mark>5p</mark> F
С	Active High	316Ω	348Ω	5pF
	Active Low	316Ω	348Ω	5pF



 $^{\star}\text{C}_{\, \text{L}}$  INCLUDES TEST FIXTURE AND PROBE CAPACITANCE



## **Electronic Signature**

An electronic signature is provided in every GAL16LV8 device. It contains 64 bits of reprogrammable memory that can contain user defined data. Some uses include user ID codes, revision numbers, or inventory control. The signature data is always available to the user independent of the state of the security cell.

NOTE: The electronic signature is included in checksum calculations. Changing the electronic signature will alter the checksum.

## **Security Cell**

A security cell is provided in the GAL16LV8 devices to prevent unauthorized copying of the array patterns. Once programmed, this cell prevents further read access to the functional bits in the device. This cell can only be erased by re-programming the device, so the original configuration can never be examined once this cell is programmed. The Electronic Signature is always available to the user, regardless of the state of this control cell.

## **Latch-Up Protection**

GAL16LV8 devices are designed with an on-board charge pump to negatively bias the substrate. The negative bias minimizes the potential of latch-up caused by negative input undershoots.

### **Device Programming**

GAL devices are programmed using a Lattice Semiconductor-approved Logic Programmer, available from a number of manufacturers. Complete programming of the device takes only a few seconds. Erasing of the device is transparent to the user, and is done automatically as part of the programming cycle.

## **Output Register Preload**

When testing state machine designs, all possible states and state transitions must be verified in the design, not just those required in the normal machine operations. This is because, in system operation, certain events occur that may throw the logic into an illegal state (power-up, line voltage glitches, brown-outs, etc.). To test a design for proper treatment of these conditions, a way must be provided to break the feedback paths, and force any desired (i.e., illegal) state into the registers. Then the machine can be sequenced and the outputs tested for correct next state conditions.

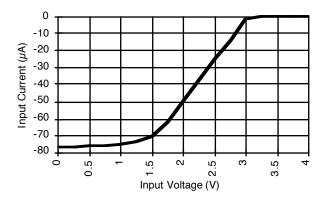
GAL16LV8 devices include circuitry that allows each registered output to be synchronously set either high or low. Thus, any present state condition can be forced for test sequencing. If necessary, approved GAL programmers capable of executing text vectors perform output register preload automatically.

### Input Buffers

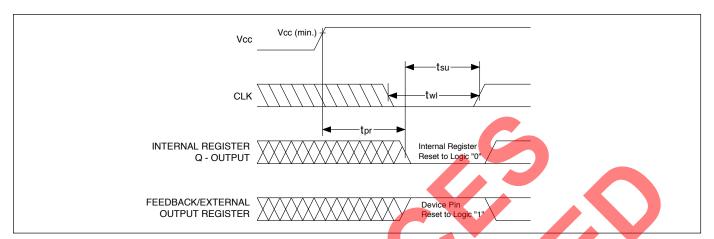
GAL16LV8 devices are designed with TTL level compatible input buffers. These buffers have a characteristically high impedance, and present a much lighter load to the driving logic than bipolar TTL devices.

The GAL16LV8D input and I/O pins have built-in active pull-ups. As a result, unused inputs and I/O's will float to a TTL "high" (logical "1"). Lattice Semiconductor recommends that all unused inputs and tri-stated I/O pins be connected to another active input,  $V_{\rm CC}$ , or Ground. Doing this will tend to improve noise immunity and reduce I<sub>CC</sub> for the device.

#### Typical Input Pull-up Characteristic (GAL16LV8D)



## **Power-Up Reset**



Circuitry within the GAL16LV8 provides a reset signal to all registers during power-up. All internal registers will have their Q outputs set low after a specified time (tpr,  $1\mu s$  MAX). As a result, the state on the registered output pins (if they are enabled) will always be high on power-up, regardless of the programmed polarity of the output pins. This feature can greatly simplify state machine design by providing a known state on power-up. Because of the asynchronous nature of system power-up, some

**Typical Input** 

conditions must be met to provide a valid power-up reset of the device. First, the Vcc rise must be monotonic. Second, the clock input must be at static TTL level as shown in the diagram during power up. The registers will reset within a maximum of tpr time. As in normal system operation, avoid clocking the device until all input and feedback path setup times have been met. The clock must also meet the minimum pulse width requirements.

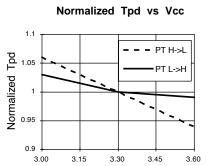
**Typical Output** 

## Input/Output Equivalent Schematics PIN Feedback Active Pull-up Circuit Active Pull-up Circuit (GAL16LV8D Only) (GAL16LV8D Only) Vcc Tri-State Vref Vref Control ESD Protection Circuit PIN Data PIN Output **ESD** Protection Circuit Feedback (To Input Buffer) Typ. Vref = Vcc Typ. Vref = Vcc

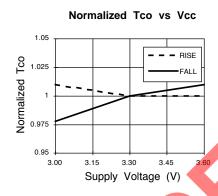


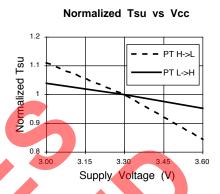


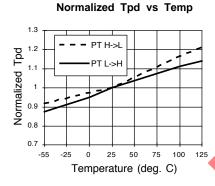
## **GAL16LV8D: Typical AC and DC Characteristic Diagrams**

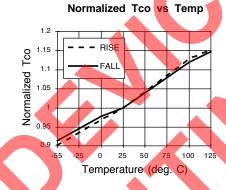


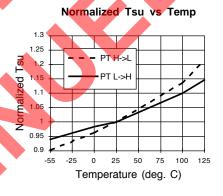
Supply Voltage (V)

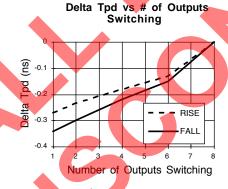


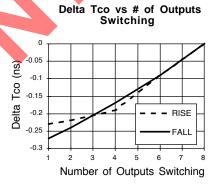


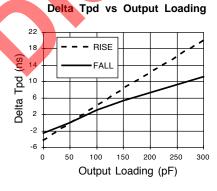


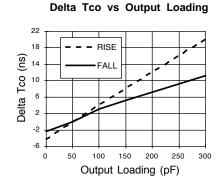








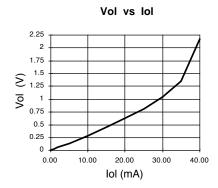


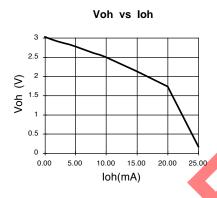


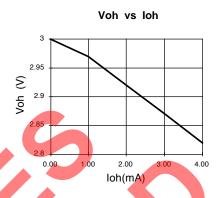


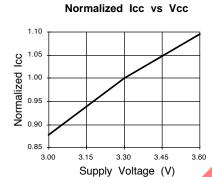


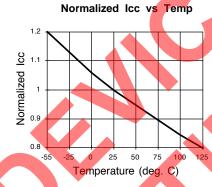
## GAL16LV8D: Typical AC and DC Characteristic Diagrams

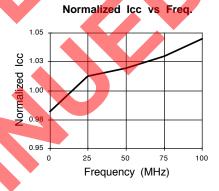


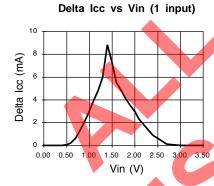


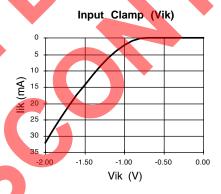








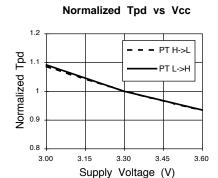


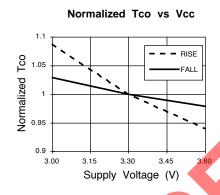


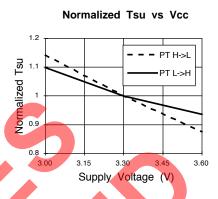


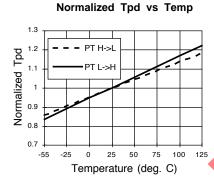


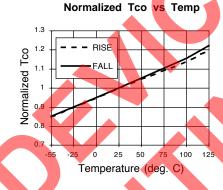
## **GAL16LV8C: Typical AC and DC Characteristic Diagrams**

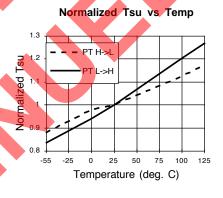


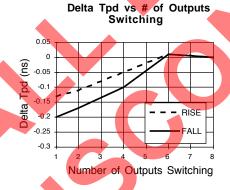


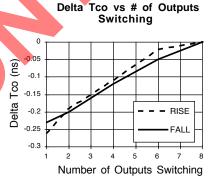


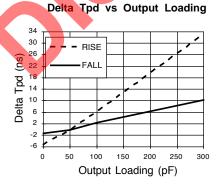


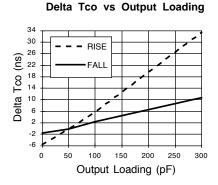
















# GAL16LV8C: Typical AC and DC Characteristic Diagrams

